

SANYO

No.2254

2SA1480/2SC3790

PNP/NPN Epitaxial Planar Type
Silicon Transistors

HIGH-DEFINITION CRT DISPLAY
VIDEO OUTPUT APPLICATIONS

Features

- High breakdown voltage ($V_{CEO} \geq 300V$)
- Small reverse transfer capacitance and excellent high frequency characteristic
 $c_{re} = 1.8pF$ (NPN), $2.3pF$ (PNP)
- Adoption of MBIT process

(): 2SA1480

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector-to-Base Voltage	V_{CB0}	(-)300	V
Collector-to-Emitter Voltage	V_{CEO}	(-)300	V
Emitter-to-Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)100	mA
Peak Collector Current	i_{cp}	(-)200	mA
Collector Dissipation	P_C	1.5	W
		7	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

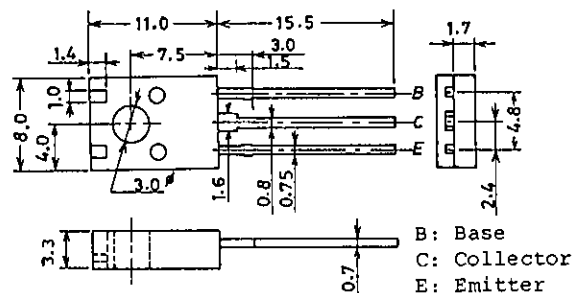
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB} = (-)200V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = (-)10V, I_C = (-)10mA$	40*		320*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)30V, I_C = (-)10mA$		150		MHz
Output Capacitance	c_{ob}	$V_{CB} = (-)30V, f = 1MHz$		2.6		pF
				(3.1)		
Reverse Transfer Capacitance	c_{re}	$V_{CB} = (-)30V, f = 1MHz$		1.8		pF
				(2.3)		
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)1.0	V

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Package Dimensions 2042A

(unit: mm)



SANYO: TO126ML

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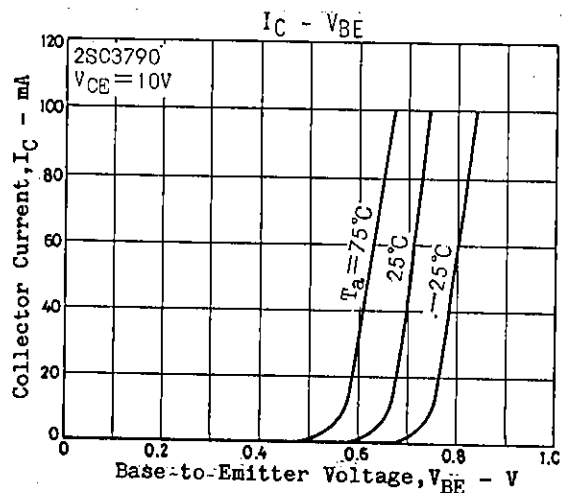
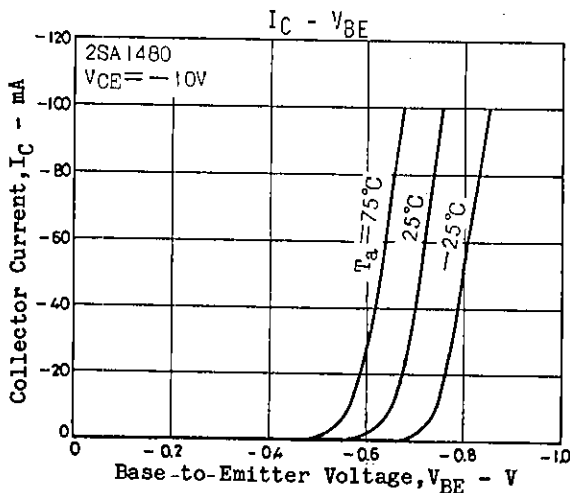
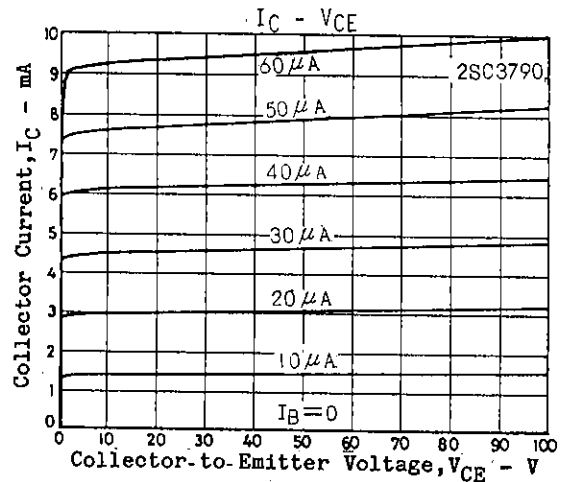
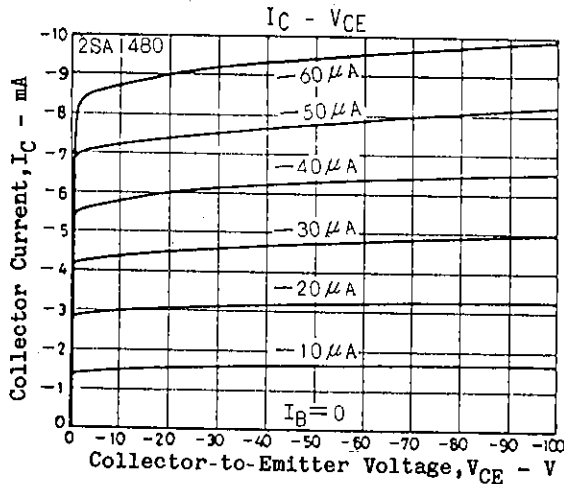
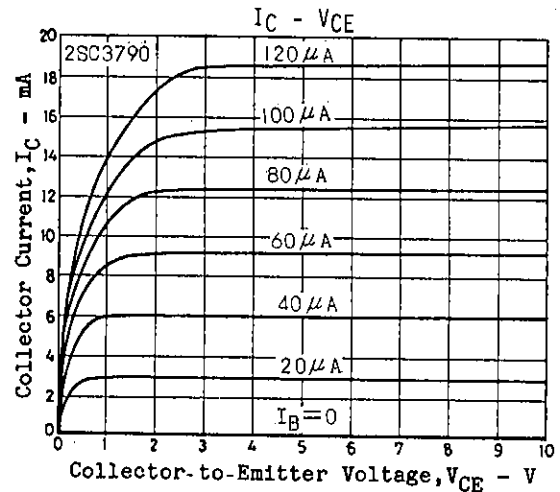
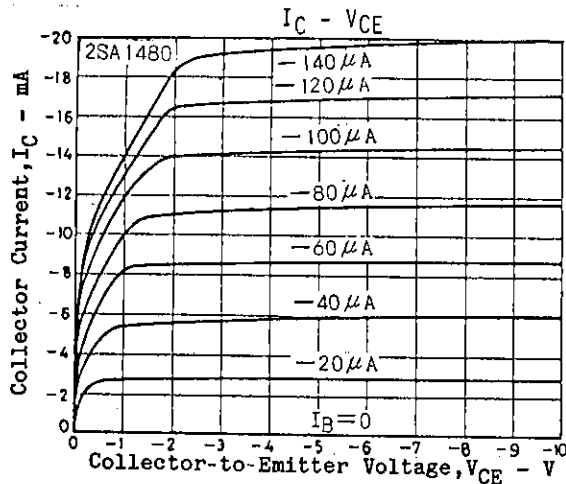
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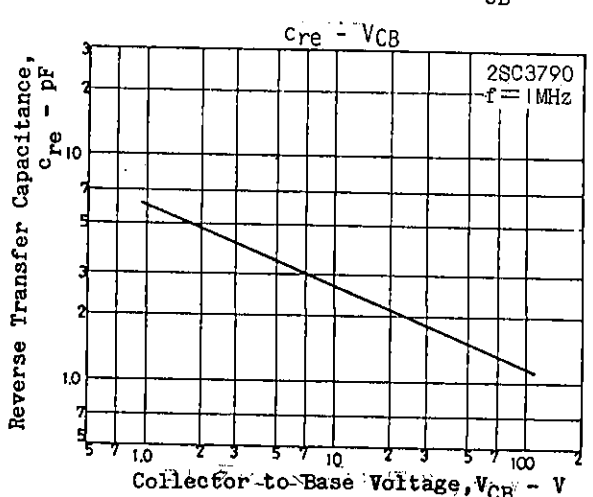
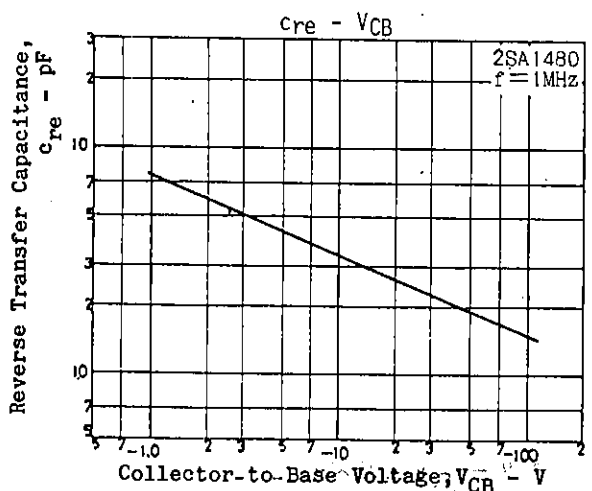
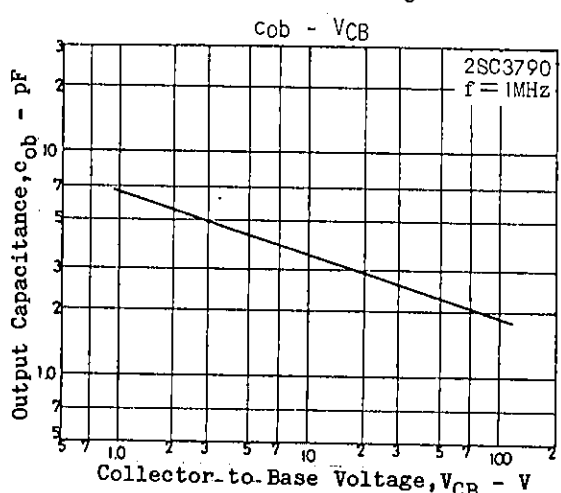
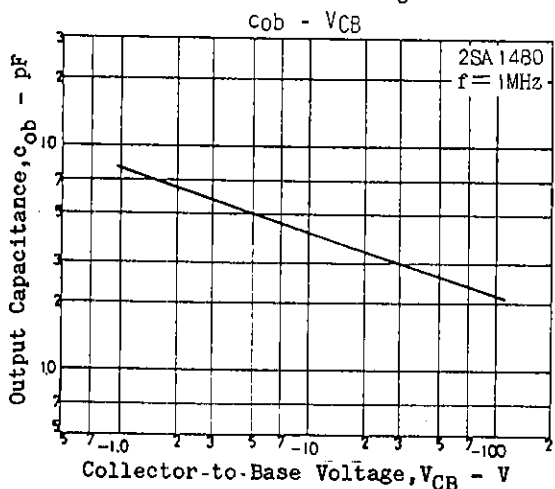
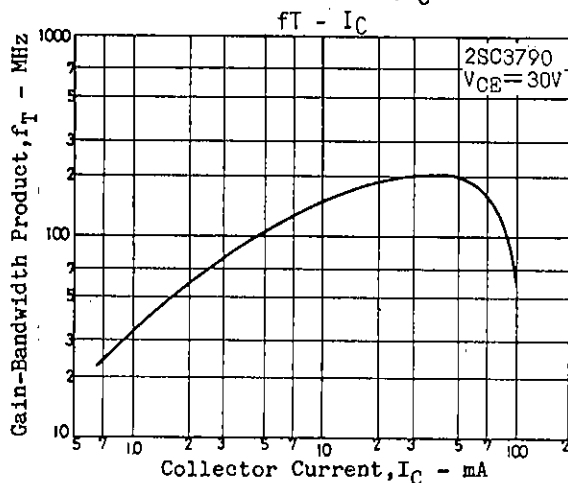
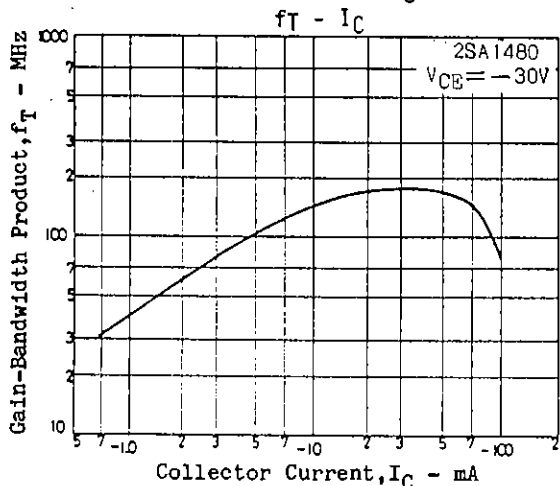
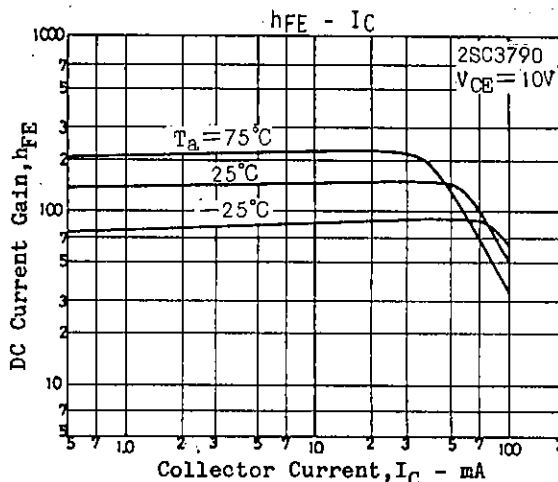
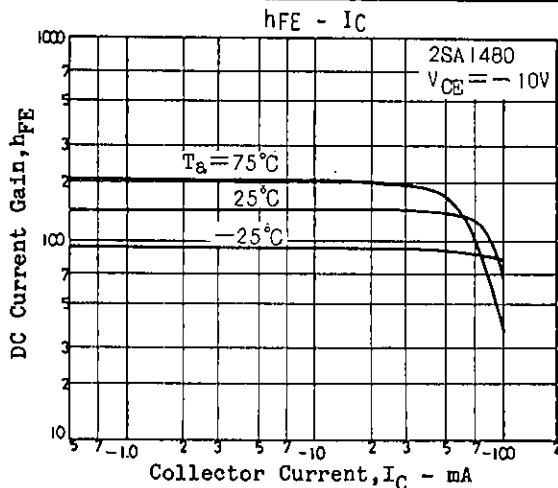
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-) 10\mu A, I_E = 0$	(-)	300		V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-) 1mA, R_{BE} = \infty$	(-)	300		V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-) 10\mu A, I_C = 0$	(-)	5		V

*: The 2SA1480/2SC3790 are classified by 10mA h_{FE} as follows:

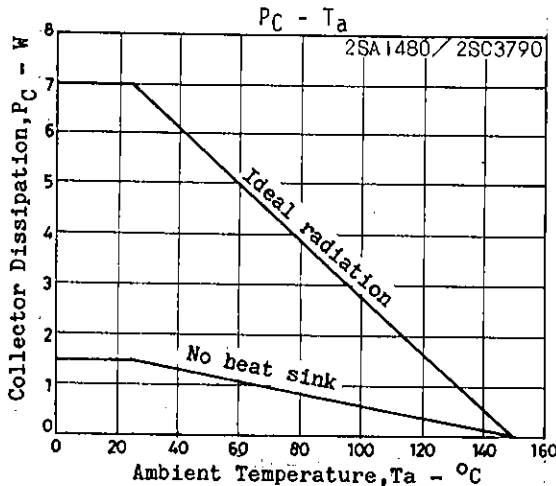
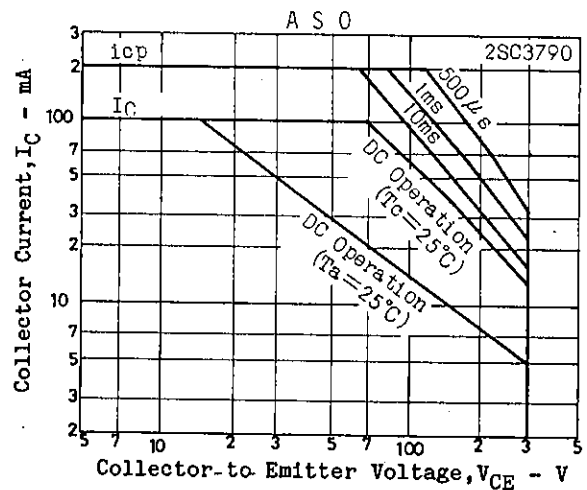
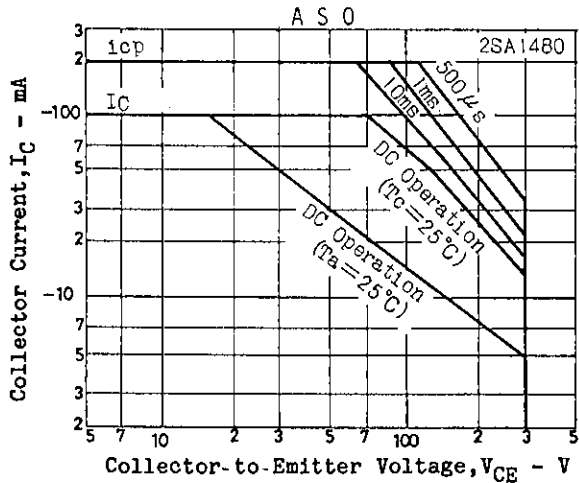
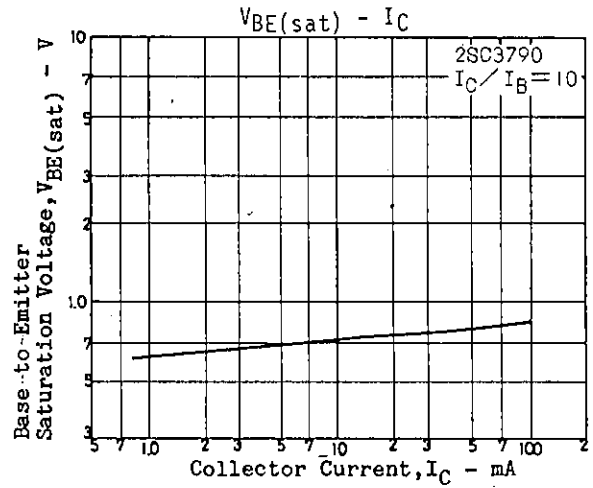
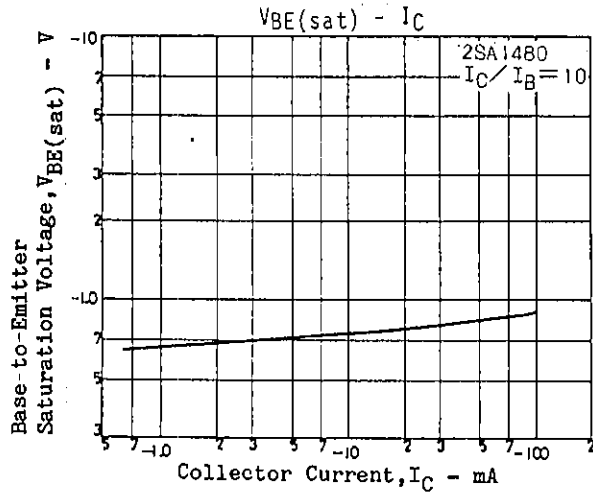
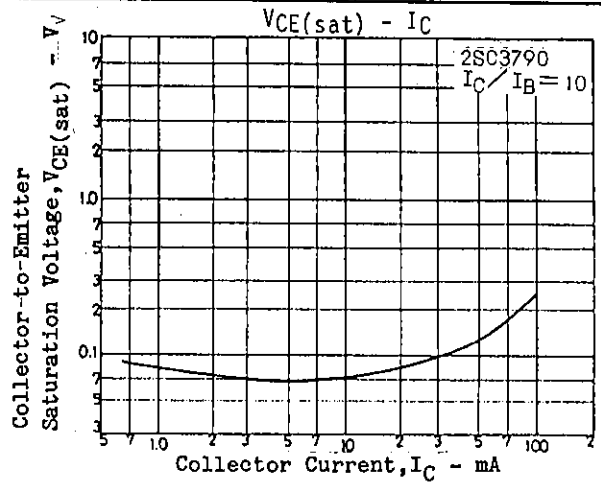
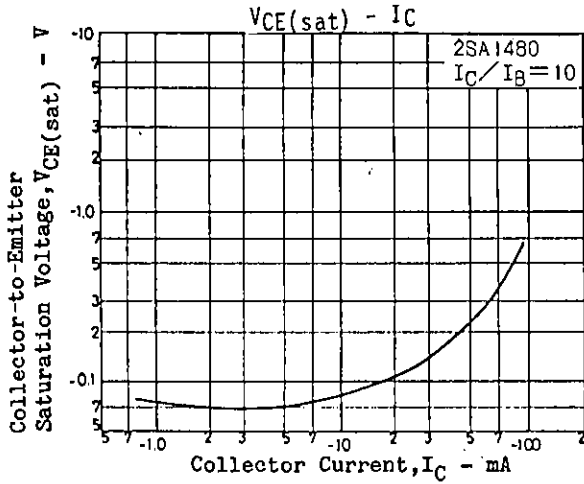
40	C	80	60	D	120	100	E	200	160	F	320
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2SA1480/2SC3790



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